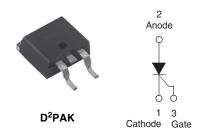




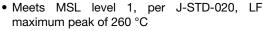
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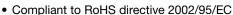
## Surface Mountable Phase Control SCR, 16 A

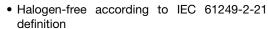


| PRODUCT SUMMARY        |              |  |  |  |  |  |
|------------------------|--------------|--|--|--|--|--|
| V <sub>T</sub> at 10 A | < 1.4 V      |  |  |  |  |  |
| I <sub>TSM</sub>       | 200 A        |  |  |  |  |  |
| V <sub>RRM</sub>       | 800 V/1200 V |  |  |  |  |  |

### **FEATURES**







• Designed and qualified for industrial level





ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### **DESCRIPTION**

The VS-16TTS..SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS                                |      |      |   |  |  |  |  |  |  |
|---|------|------|---|--|--|--|--|--|--|
| APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS             |      |      |   |  |  |  |  |  |  |
| NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper | 2.5  | 3.5  |   |  |  |  |  |  |  |
| Aluminum IMS, R <sub>thCA</sub> = 15 °C/W                             | 6.3  | 9.5  | А |  |  |  |  |  |  |
| Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W                | 14.0 | 18.5 |   |  |  |  |  |  |  |

#### Note

T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

| MAJOR RATINGS AND CHARACTERISTICS |                              |             |       |  |  |  |  |  |  |
|-----------------------------------|------------------------------|-------------|-------|--|--|--|--|--|--|
| SYMBOL                            | CHARACTERISTICS              | VALUES      | UNITS |  |  |  |  |  |  |
| I <sub>T(AV)</sub>                | Sinusoidal waveform          | 10          | ٨     |  |  |  |  |  |  |
| I <sub>RMS</sub>                  |                              | 16          | А     |  |  |  |  |  |  |
| $V_{RRM}/V_{DRM}$                 |                              | 800/1200    | V     |  |  |  |  |  |  |
| I <sub>TSM</sub>                  |                              | 200         | Α     |  |  |  |  |  |  |
| V <sub>T</sub>                    | 10 A, T <sub>J</sub> = 25 °C | 1.4         | V     |  |  |  |  |  |  |
| dV/dt                             |                              | 500         | V/µs  |  |  |  |  |  |  |
| dl/dt                             |                              | 150         | A/μs  |  |  |  |  |  |  |
| T <sub>J</sub>                    |                              | - 40 to 125 | °C    |  |  |  |  |  |  |

| VOLTAGE RATINGS |   |  |   |  |  |  |  |  |  |  |
|-----------------|---|--|---|--|--|--|--|--|--|--|
| PART NUMBER     | V <sub>RRM</sub> , MAXIMUM PEAK<br>REVERSE VOLTAGE<br>V | V <sub>DRM</sub> , MAXIMUM PEAK<br>DIRECT VOLTAGE<br>V | I <sub>RRM</sub> /I <sub>DRM</sub><br>AT 125 °C<br>mA |  |  |  |  |  |  |  |
| VS-16TTS08SPbF  | 800   | 800  | 10  |  |  |  |  |  |  |  |
| VS-16TTS12SPbF  | 1200  | 1200   | 10  |  |  |  |  |  |  |  |

Document Number: 94589 Revision: 08-Jun-10 For technical questions within your region, please contact one of the following: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

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## Surface Mountable Phase Control SCR, 16 A



| ABSOLUTE MAXIMUM RATINGS                   |                                  |   |        |      |                  |  |  |
|--|----------------------------------|---|--------|------|------------------|--|--|
| PARAMETER                                  | SYMBOL                           | TEST CONDITIONS   | VALUES |      | UNITS            |  |  |
| PANAMETEN                                  | STIVIDOL                         | TEST CONDITIONS   | TYP.   | MAX. | UNITS            |  |  |
| Maximum average on-state current           | I <sub>T(AV)</sub>               | T <sub>C</sub> = 98 °C, 180° conduction, half sine wave | 10     |      |                  |  |  |
| Maximum RMS on-state current               | I <sub>RMS</sub>                 |   | 1      | 6    | Α                |  |  |
| Maximum peak, one-cycle,                   | <b>L</b>                         | 10 ms sine pulse, rated V <sub>RRM</sub> applied        | 17     | 70   | A                |  |  |
| non-repetitive surge current               | I <sub>TSM</sub>                 | 10 ms sine pulse, no voltage reapplied                  | 20     | 00   |                  |  |  |
| Maximum I <sup>2</sup> t for fusing        | I <sup>2</sup> t                 | 10 ms sine pulse, rated V <sub>RRM</sub> applied        | 14     | 14   | A <sup>2</sup> s |  |  |
| Maximum i-t for fusing                     | 1-1                              | 10 ms sine pulse, no voltage reapplied                  | 200    |      | A-5              |  |  |
| Maximum I $^2\sqrt{t}$ for fusing          | I²√t                             | t = 0.1 ms to 10 ms, no voltage reapplied               | 2000   |      | A²√s             |  |  |
| Maximum on-state voltage drop              | $V_{TM}$                         | 10 A, T <sub>J</sub> = 25 °C                            | 1      | .4   | ٧                |  |  |
| On-state slope resistance                  | r <sub>t</sub>                   | T <sub>.I</sub> = 125 °C                                |        | 24.0 |                  |  |  |
| Threshold voltage                          | $V_{T(TO)}$                      | 1] = 123 0  | 1.1    |      | ٧                |  |  |
| Maximum rayaraa and direct laakaga aurrant | 1 //                             | $T_J = 25 ^{\circ}\text{C}$                             | 0.5    |      | mA               |  |  |
| Maximum reverse and direct leakage current | I <sub>RM</sub> /I <sub>DM</sub> | $V_R = Rated V_{RRM}/V_{DRM}$                           | 10     |      |                  |  |  |
| Holding current                            | I <sub>H</sub>                   | Anode supply = 6 V, resistive load, initial $I_T = 1 A$ | -      | 100  | IIIA             |  |  |
| Maximum latching current                   | ΙL                               | Anode supply = 6 V, resistive load                      | 20     | 00   |                  |  |  |
| Maximum rate of rise of off-state voltage  | dV/dt                            |   |        | 00   | V/µs             |  |  |
| Maximum rate of rise of turned-on current  | dl/dt                            |   | 1:     | 50   | A/µs             |  |  |

| TRIGGERING                                  |                    |  |        |       |  |  |  |
|---|--------------------|--|--------|-------|--|--|--|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS  | VALUES | UNITS |  |  |  |
| Maximum peak gate power                     | P <sub>GM</sub>    |  | 8.0    | W     |  |  |  |
| Maximum average gate power                  | P <sub>G(AV)</sub> |  | 2.0    | VV    |  |  |  |
| Maximum peak positive gate current          | + I <sub>GM</sub>  |  | 1.5    | Α     |  |  |  |
| Maximum peak negative gate voltage          | - V <sub>GM</sub>  |  | 10     | V     |  |  |  |
|   | I <sub>GT</sub>    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C | 90     | mA    |  |  |  |
| Maximum required DC gate current to trigger |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 60     |       |  |  |  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 35     |       |  |  |  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C | 3.0    |       |  |  |  |
| Maximum required DC gate voltage to trigger | $V_{\mathrm{GT}}$  | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 2.0    | v     |  |  |  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 1.0    | V     |  |  |  |
| Maximum DC gate voltage not to trigger V    |                    | T = 125 °C V = Peted value                                   | 0.25   |       |  |  |  |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>    | T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value      | 2.0    | mA    |  |  |  |

| SWITCHING                                  |                 |                          |     |    |  |  |  |
|--|-----------------|--------------------------|-----|----|--|--|--|
| PARAMETER SYMBOL TEST CONDITIONS VALUES UN |                 |                          |     |    |  |  |  |
| Typical turn-on time                       | t <sub>gt</sub> | T <sub>J</sub> = 25 °C   | 0.9 |    |  |  |  |
| Typical reverse recovery time              | t <sub>rr</sub> | T <sub>.I</sub> = 125 °C | 4   | μs |  |  |  |
| Typical turn-off time                      | t <sub>q</sub>  | 1j = 125 G               | 110 |    |  |  |  |

### Surface Mountable Phase Control SCR, 16 A

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| THERMAL - MECHANICAL SPECIFICATIONS             |                                   |   |             |      |  |  |  |  |
|---|-----------------------------------|---|-------------|------|--|--|--|--|
| PARAMETER                                       | ER SYMBOL TEST CONDITIONS         |   |             |      |  |  |  |  |
| Maximum junction and storage temperature range  | T <sub>J</sub> , T <sub>Stg</sub> |   | - 40 to 125 | °C   |  |  |  |  |
| Soldering temperature                           | T <sub>S</sub>                    | For 10 s (1.6 mm from case)             | 240         |      |  |  |  |  |
| Maximum thermal resistance, junction to case    | R <sub>thJC</sub>                 | DC operation                            | 1.3         | °C/W |  |  |  |  |
| Typical thermal resistance, junction to ambient | R <sub>thJA</sub>                 | PCB mount (1)                           | 40          | C/VV |  |  |  |  |
| Approximate weight                              |                                   |   | 2           | g    |  |  |  |  |
| Approximate weight                              |                                   |   | 0.07        | oz.  |  |  |  |  |
| Marking device                                  |                                   | Case style D <sup>2</sup> PAK (SMD-220) | 16TTS08S    |      |  |  |  |  |
| Marking device                                  |                                   | Case style D FAR (SIVID-220)            | 16TTS12S    |      |  |  |  |  |

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

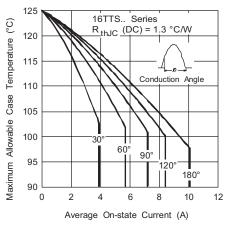


Fig. 1 - Current Rating Characteristics

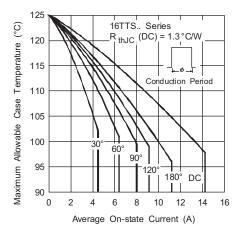


Fig. 2 - Current Rating Characteristics

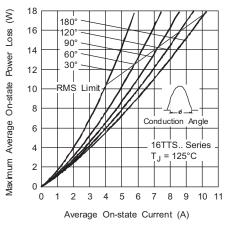


Fig. 3 - On-State Power Loss Characteristics

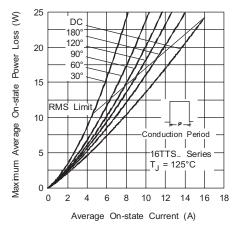


Fig. 4 - On-State Power Loss Characteristics

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## Surface Mountable Phase Control SCR, 16 A



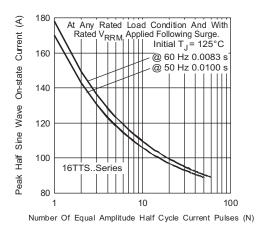


Fig. 5 - Maximum Non-Repetitive Surge Current

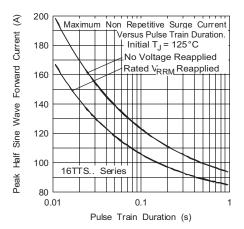


Fig. 6 - Maximum Non-Repetitive Surge Current

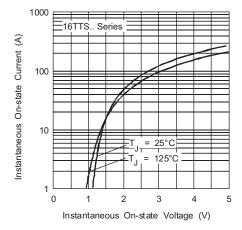


Fig. 7 - On-State Voltage Drop Characteristics

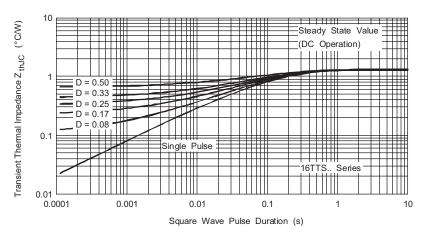


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics



### Surface Mountable Phase Control SCR, 16 A

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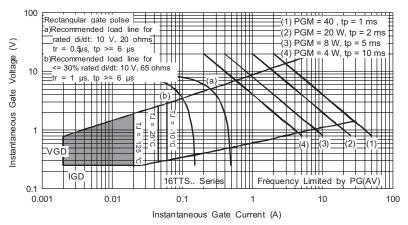
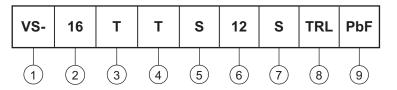


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 HPP product suffix
- 2 Current rating
- 3 Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AC

5 - Type of silicon:

S = Standard recovery rectifier

- 6 Voltage rating: Voltage code x 100 = V<sub>RRM</sub> 08 = 800 V 12 = 1200 V
- 7 S = TO-220 D<sup>2</sup>PAK (SMD-220) version
- 8 • None = Tube
  - TRL = Tape and reel (left oriented)
  - TRR = Tape and reel (right oriented)
- 9 PbF = Lead (Pb)-free

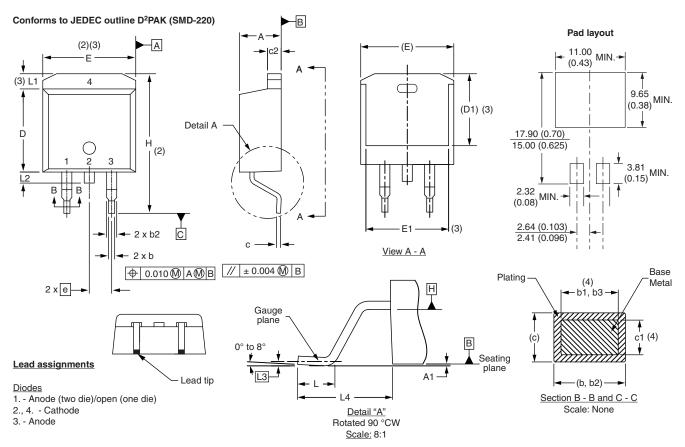
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?95046 |  |  |  |  |  |
| Part marking information   | www.vishay.com/doc?95054 |  |  |  |  |  |
| Packaging information      | www.vishay.com/doc?95032 |  |  |  |  |  |



## Vishay Semiconductors

## D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



| SYMBOL  | MILLIMETERS |       | INC   | HES   | NOTES |       | SYMBOL   | MILLIN | IETERS | INC   | HES   | NOTES |
|---------|-------------|-------|-------|-------|-------|-------|----------|--------|--------|-------|-------|-------|
| STWIBOL | MIN.        | MAX.  | MIN.  | MAX.  | NOTES | NOTES | STINIBUL | MIN.   | MAX.   | MIN.  | MAX.  | NOTES |
| Α       | 4.06        | 4.83  | 0.160 | 0.190 |       |       | D1       | 6.86   | 8.00   | 0.270 | 0.315 | 3     |
| A1      | 0.00        | 0.254 | 0.000 | 0.010 |       |       | E        | 9.65   | 10.67  | 0.380 | 0.420 | 2, 3  |
| b       | 0.51        | 0.99  | 0.020 | 0.039 |       |       | E1       | 7.90   | 8.80   | 0.311 | 0.346 | 3     |
| b1      | 0.51        | 0.89  | 0.020 | 0.035 | 4     |       | е        | 2.54   | BSC    | 0.100 | ) BSC |       |
| b2      | 1.14        | 1.78  | 0.045 | 0.070 |       |       | Н        | 14.61  | 15.88  | 0.575 | 0.625 |       |
| b3      | 1.14        | 1.73  | 0.045 | 0.068 | 4     |       | L        | 1.78   | 2.79   | 0.070 | 0.110 |       |
| С       | 0.38        | 0.74  | 0.015 | 0.029 |       |       | L1       | -      | 1.65   | -     | 0.066 | 3     |
| c1      | 0.38        | 0.58  | 0.015 | 0.023 | 4     |       | L2       | 1.27   | 1.78   | 0.050 | 0.070 |       |
| c2      | 1.14        | 1.65  | 0.045 | 0.065 |       |       | L3       | 0.25   | BSC    | 0.010 | BSC   |       |
| D       | 8.51        | 9.65  | 0.335 | 0.380 | 2     | 1     | L4       | 4.78   | 5.28   | 0.188 | 0.208 |       |

#### Notes

- $^{(1)}$  Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

Document Number: 95046 Revision: 31-Mar-11

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